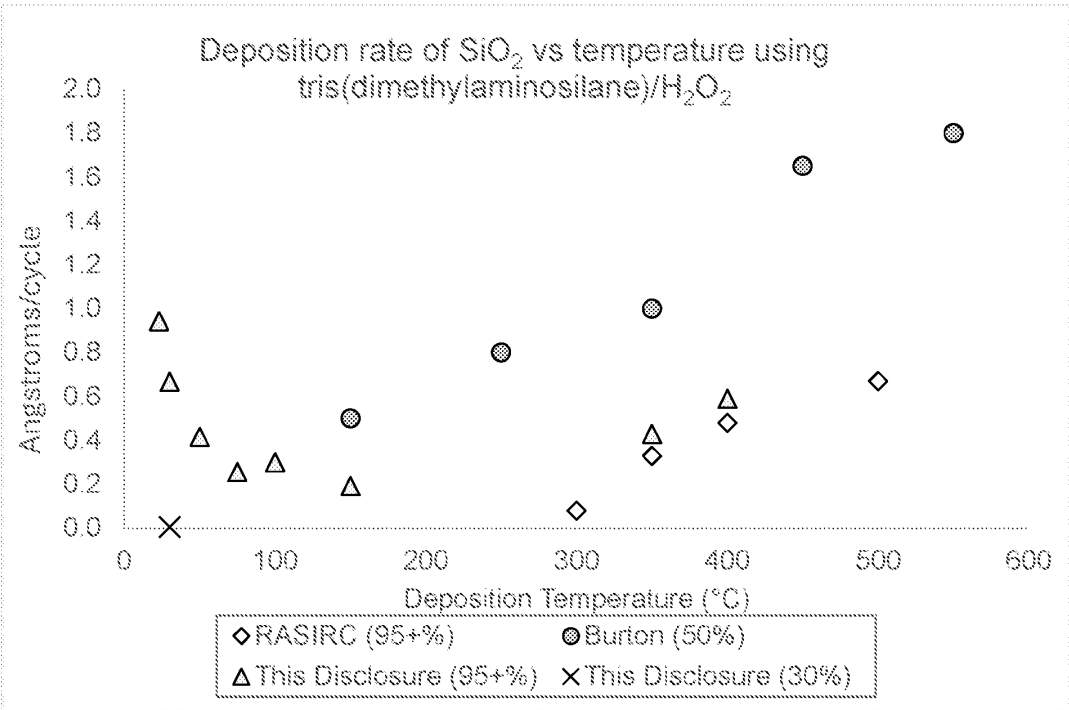
Fig. 1


Deposition rate of SiO2 vs temperature using tris(dimethylaminosilane)/H2O2
Angstroms/cycle
2.0
1.8
1.6
1.4
1.2
1.0
0.8
0.6
0.4
0.2
0.0
0
100
200
300
400
500
600
Deposition Temperature (°C)
RASIRC (95+%)
Burton (50%)
This Disclosure (95+%)
This Disclosure (30%)